

# Switching (60V, 10A)

## 2SK2095N

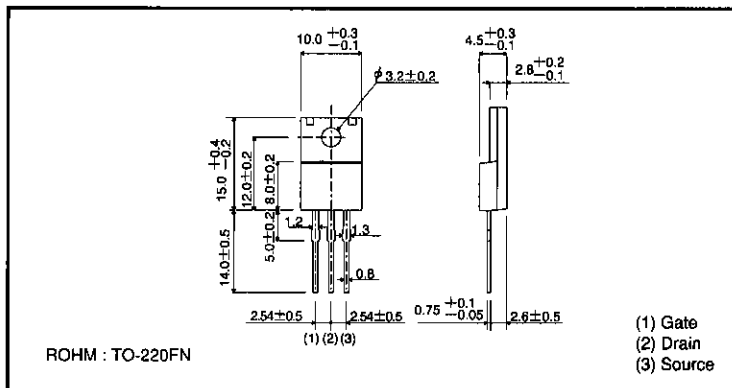
●Features

- 1) Low on-resistance.
- 2) High-speed switching.
- 3) Wide SOA (safe operating area).
- 4) Easily designed drive circuits.
- 5) Low  $V_{GS(th)}$ .
- 6) Easy to use in parallel.

●Structure

Silicon N-channel  
MOSFET transistor

●External dimensions (Units: mm)



MOS FET

●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter  | Symbol     | Limits         | Unit             |   |
|--|------------|----------------|------------------|---|
| Drain-source voltage                               | $V_{DS}$   | 60             | V                |   |
| Gate-source voltage                                | $V_{GS}$   | $\pm 20$       | V                |   |
| Drain current                                      | Continuous | $I_D$          | 10               | A |
|  | Pulsed     | $I_{DP}^*$     | 40               | A |
| Drain reverse current                              | Continuous | $I_{DR}$       | 10               | A |
|  | Pulsed     | $I_{DRP}^*$    | 40               | A |
| Total power dissipation ( $T_c=25^\circ\text{C}$ ) | $P_D$      | 30             | W                |   |
| Channel temperature                                | $T_{ch}$   | 150            | $^\circ\text{C}$ |   |
| Storage temperature                                | $T_{stg}$  | $-55 \sim 150$ | $^\circ\text{C}$ |   |

\*  $P_w \leq 10 \mu\text{s}$ , Duty cycle  $\leq 1\%$

●Packaging specifications

| Type     | Package                      | Bulk |
|----------|------------------------------|------|
|          | Code                         | —    |
|          | Basic ordering unit (pieces) | 500  |
| 2SK2095N |                              | ○    |

●Electrical characteristics (Ta = 25°C)

| Parameter                        | Symbol               | Min. | Typ.  | Max.  | Unit | Conditions                                 |
|----------------------------------|----------------------|------|-------|-------|------|--|
| Gate leakage current             | I <sub>GSS</sub>     | —    | —     | ±100  | nA   | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V |
| Drain-source breakdown voltage   | V <sub>(BR)DSS</sub> | 60   | —     | —     | V    | I <sub>D</sub> =1mA, V <sub>GS</sub> =0V   |
| Drain cutoff current             | I <sub>DSS</sub>     | —    | —     | 100   | μA   | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V  |
| Gate threshold voltage           | V <sub>GS(th)</sub>  | 1    | —     | 2.5   | V    | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA  |
| Drain-source on-state resistance | R <sub>DS(on)</sub>  | —    | 0.080 | 0.095 | Ω    | I <sub>D</sub> =5A, V <sub>GS</sub> =10V   |
|                                  |                      | —    | 0.11  | 0.14  |      | I <sub>D</sub> =5A, V <sub>GS</sub> =4V    |
| Forward propagation admittance   | Y <sub>fs</sub>  *   | 5    | —     | —     | S    | V <sub>DS</sub> =10V, I <sub>D</sub> =5A   |
| Input capacitance                | C <sub>ISS</sub>     | —    | 1600  | —     | pF   | V <sub>DS</sub> =10V                       |
| Output capacitance               | C <sub>OSS</sub>     | —    | 600   | —     | pF   | V <sub>GS</sub> =0V                        |
| Reverse transfer capacitance     | C <sub>RSS</sub>     | —    | 150   | —     | pF   | f=1MHz                                     |
| Turn-on delay time               | t <sub>d(on)</sub>   | —    | 30    | —     | ns   | I <sub>D</sub> =5A, V <sub>DD</sub> ≐30V   |
| Rise time                        | t <sub>r</sub>       | —    | 80    | —     | ns   | V <sub>GS</sub> =10V                       |
| Turn-off delay time              | t <sub>d(off)</sub>  | —    | 300   | —     | ns   | R <sub>L</sub> =6Ω                         |
| Fall time                        | t <sub>f</sub>       | —    | 100   | —     | ns   | R <sub>G</sub> =10Ω                        |

\* Pw≦300 μs, Duty cycle≦1%

●Electrical characteristic curves

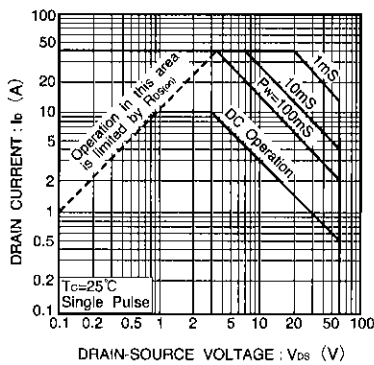


Fig.1 Maximum Safe Operating Area

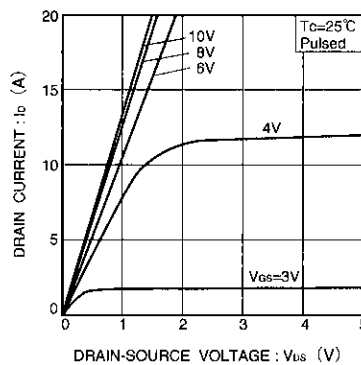


Fig.2 Typical Output Characteristics

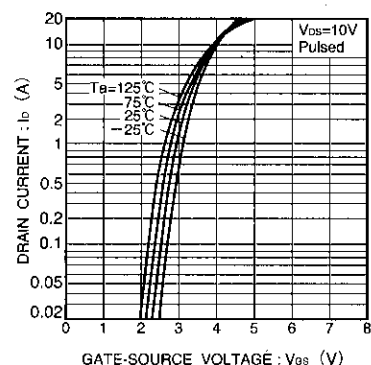


Fig.3 Typical Transfer Characteristics

● Electrical characteristic curves

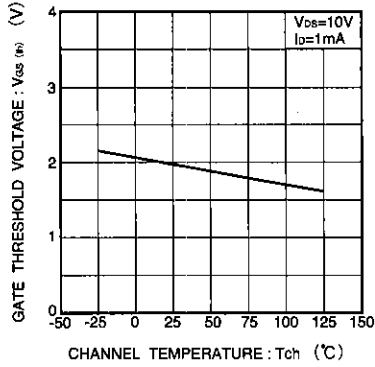


Fig.4 Gate Threshold Voltage vs. Channel Temperature

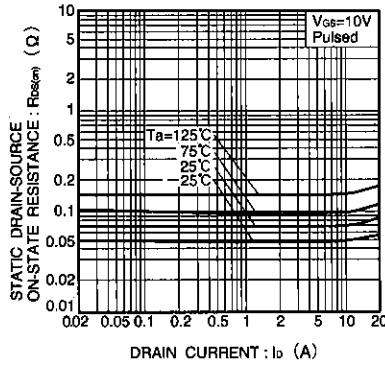


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (I)

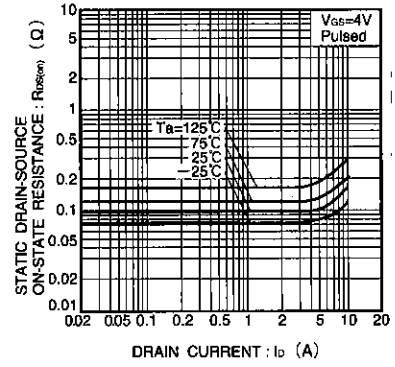


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current (II)

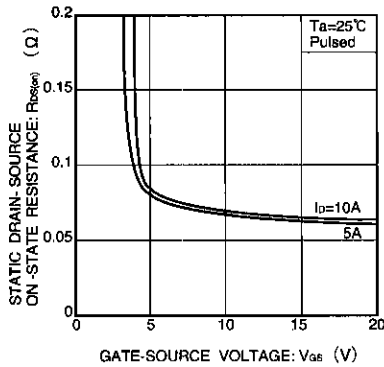


Fig.7 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

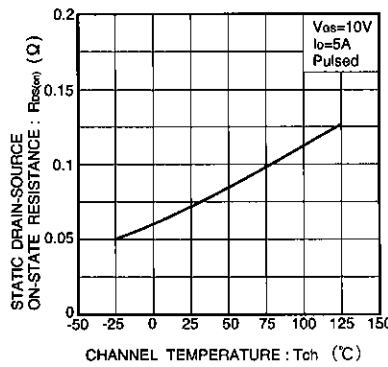


Fig.8 Static Drain-Source On-State Resistance vs. Channel Temperature

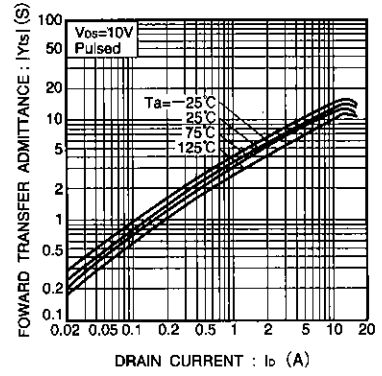


Fig.9 Forward Transfer Admittance vs. Drain Current

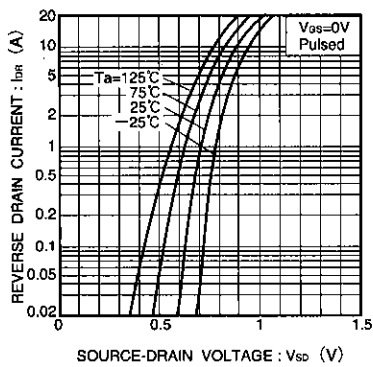


Fig.10 Reverse Drain Current vs. Source-Drain Voltage (I)

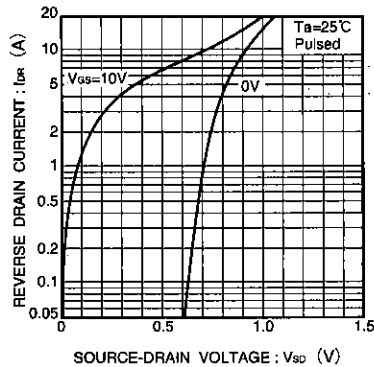


Fig.11 Reverse Drain Current vs. Source-Drain Voltage (II)

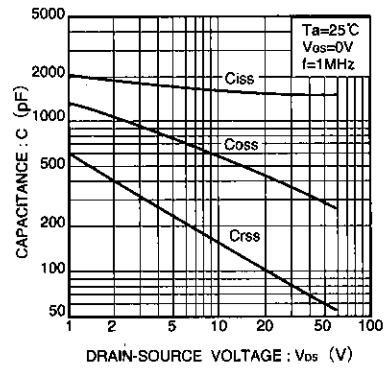


Fig.12 Typical Capacitance vs. Drain-Source Voltage

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●Electrical characteristic curves

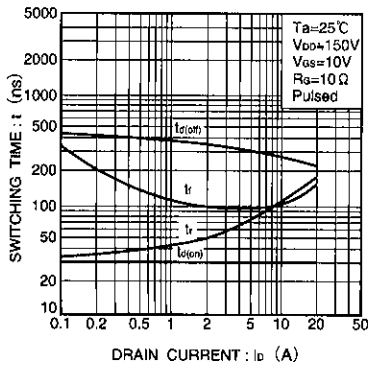


Fig.13 Switching Characteristics  
(See Figure. 15 and 16 for measurement circuits)

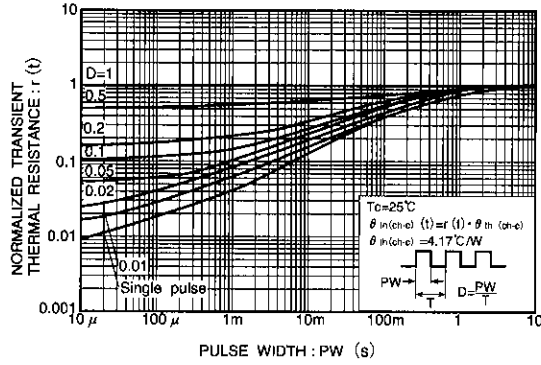


Fig.14 Normalized Transient Thermal Resistance vs.Pulse Width

●Switching characteristics measurement circuit

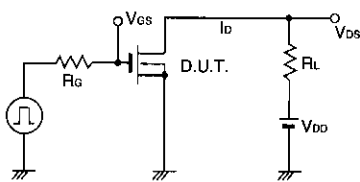


Fig.15 Switching Time Measurement Circuit

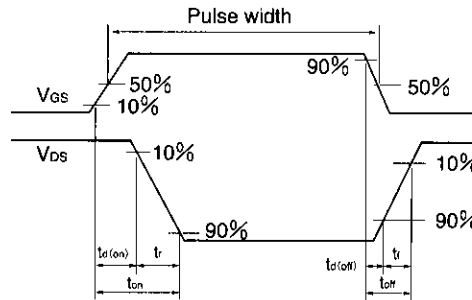


Fig.16 Switching Time Waveforms

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